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## AUTHOR'S RELEVANT PUBLICATIONS

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### Journals:

1. **Ekta Goel**, Sanjay Kumar, Kunal Singh, Balraj Singh, Mirgender Kumar, and Satyabrata Jit, “2-D Analytical Modeling of Threshold Voltage for Graded-Channel Dual-Material Double-Gate MOSFETs”, *IEEE Transactions on Electron Devices*, vol. 63, pp. 966-973, (2016).
2. **Ekta Goel**, Sanjay Kumar, Balraj Singh, Kunal Singh, Satyabrata Jit, “Two-dimensional model for subthreshold current and subthreshold swing of graded-channel dual-material double gate (GCDMDG) MOSFETs”, *Superlattices and Microstructures*, vol. 106, pp. 147-155, (2017).
3. **Ekta Goel**, Balraj Singh, Sanjay Kumar, Kunal Singh, and Satyabrata Jit, “Analytical threshold voltage modeling of ion-implanted strained-Si double material double-gate (DMDG) MOSFETs”, *Indian Journal of Physics*, vol. 91, pp. 383-390, (2017).
4. **Ekta Goel**, Kunal Singh, Balraj Singh, Sanjay Kumar, and Satyabrata Jit, “2-D Analytical Modeling of Subthreshold Current and Subthreshold Swing for Ion-Implanted Strained-Si Double-Material Double-Gate (DMDG) MOSFETs”, *Indian Journal of Physics*, vol. 91, pp.1069–1076, (2017).

### International Conference:

1. **Ekta Goel**, Sanjay Kumar, Kunal Singh, Balraj Singh and S. Jit, “An Analytical Model for Threshold Voltage Roll-off of Graded-Channel Dual-Material Double-Gate MOSFETs”, *International Conference on Nanoscience & Nanotechnology (ICNN-2017)*, 22nd-24th September, 2017 held at Babasaheb Bhimrao Ambedkar University, Lucknow, U.P., India.
2. **Ekta Goel**, Kunal Singh, Sanjay Kumar, Balraj Singh, M. Kumar and S. Jit, “Impact of Heterogeneous Gate Dielectric on Strained Silicon Double-Gate Tunnel Field Effect Transistor”, *18<sup>th</sup> International Workshop on the Physics of Semiconductor Devices (IWPSD)*, @Indian Institute of Science, Bangalore, 2015.